

序号	试验项目 (Test Item)	试验条件 (Condition)	抽样数 (Sample size)	判定标准 (Decision)	试验依据 (Reference)
1	高温反偏 (High Temperature Reverse Bias)	a、Voltage: 80% Rated Voltage; b、Time: 168h/1000h; c、Temperature: Fast Recovery Diode or Thyristor: 125°C; Discrete Device, MOSFET or IGBT: 145°C; Rectifier Diode: 150°C.	5PCS (FG)	LSL≤Electrical Parameter≤USL	IEC 60747
2	高温栅偏 (High Temperature Grating Bias)	a、Voltage: ±V _{GSmax} /V _{GEmax} ; b、Temperature: T _{stgmax} ; c、Time: 168h/1000h.	5PCS (FG)	LSL≤Electrical Parameter≤USL	IEC 60747
3	温度循环 (Temperature Cycling)	a、Temperature: Low Temperature -55°C for 30min; High Temperature 150°C for 30min; b、Conversion Time: 10s; c、Cycle Times: 10Times/100Times.	5PCS (FG)	LSL≤Electrical Parameter≤USL	IEC 60068-2-14 Test Na
4	恒温恒湿 (Constant Temperature and Humidity)	a、Temperature: 85°C; b、Humidity: 85% RH; c、Time: 168h/1000h.	5PCS (FG)	LSL≤Electrical Parameter≤USL	IEC 60068-2-67
5	功率循环 (Power Cycling)	a、ΔT _J =100°C+15/-10°C; b、Cycle Times: 100Times/1000Times.	5PCS (FG)	LSL≤Electrical Parameter≤USL	IEC 60749-34
6	高温存储 (High Temperature Storage)	a、Temperature: T _{stgmax} ; b、Time: 168H/1000H.	5PCS (FG)	LSL≤Electrical Parameter≤USL	IEC 60068-2-2
7	低温存储 (Low Temperature storage)	a、Temperature: T _{stgmin} ; b、Time: 168H/1000H.	5PCS (FG)	LSL≤Electrical Parameter≤USL	IEC 60068-2-1
8	冲击试验 (Shock Test)	a、Max.: 50G; b、Pulse Time: 6ms, Sine Half Wave; c、Dir.: X / Y / Z, 3 Positive and 3 Negative Impacts, 18Times in total.	5PCS (FG)	LSL≤Electrical Parameter≤USL	IEC 60068-2-27 Test Ea
9	震动试验 (Vibration Test)	a、Vibration Waveform: 5~200 Hz, Sine Wave; b、Acceleration: 5g; c、Direction of Vibration: x, y, z d、Vibration Time: Frequency Sweep: 5Hz~200Hz~5Hz, 1min, 2H per axle	5PCS (FG)	LSL≤Electrical Parameter≤USL	IEC 60068-2-6 Test Fc